Supplementary Information

Improved energy storage performance of NBTM/STM multilayer films via designing the stacking order

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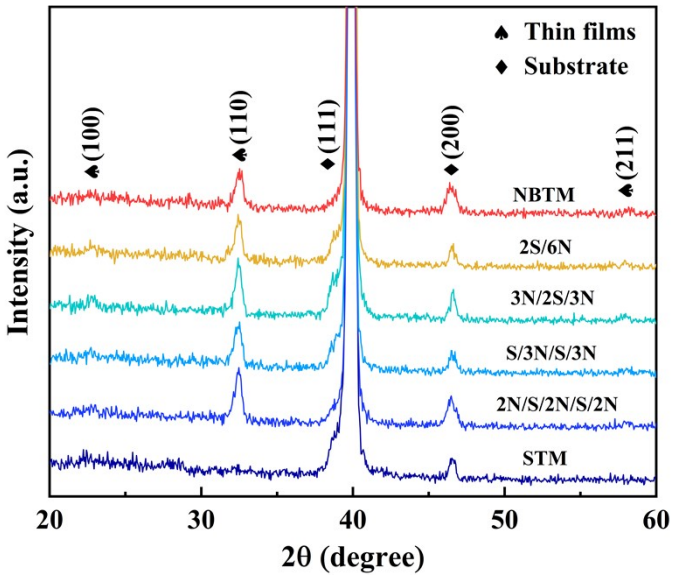

Fig. S1 The XRD spectrum of the NBTM film, NBTM/STM multilayer films, and STM film.

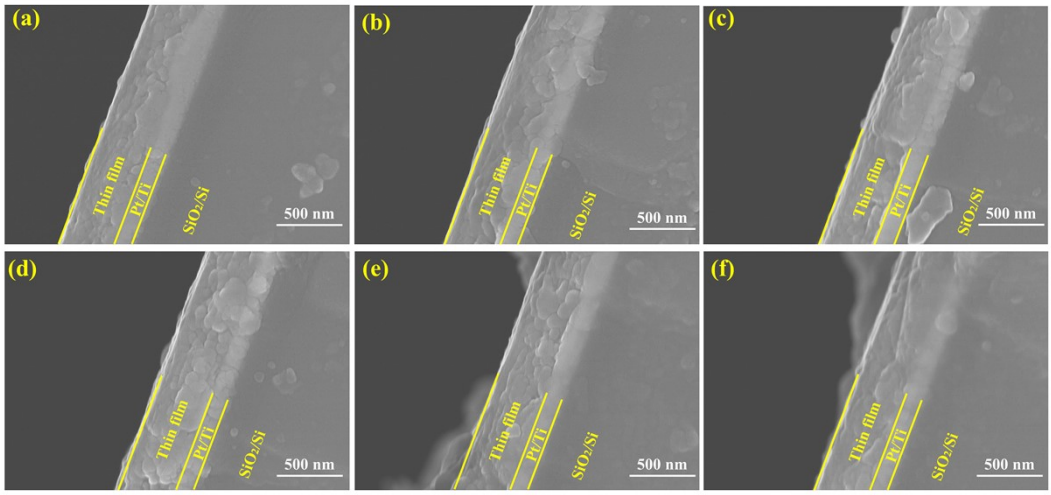

Fig. S2 Cross-section SEM images of the (a) NBTM, (b) 2S/6N, (c) 3N/2S/3N, (d) S/3N/S/3N, (e) 2N/S/2N/S/2N, and (f) STM films.

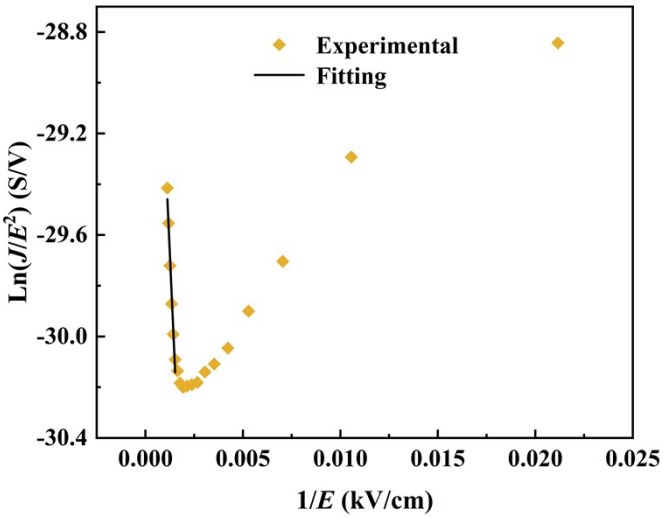

Fig. S3 Linear fitting of $1/E$ and $\ln(J/E^2)$ of the 2S/6N film.

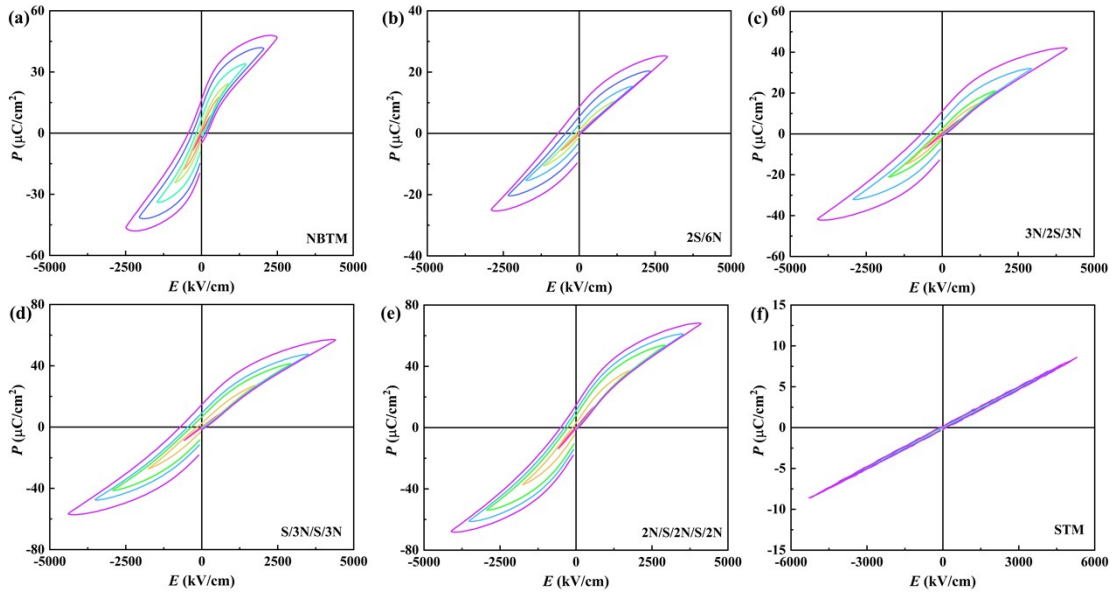

Fig. S4 *P*-*E* loops of the (a) NBTM, (b) 2S/6N, (c) 3N/2S/3N, (d) S/3N/S/3N, (e) 2N/S/2N/S/2N, and (f) STM films.

Table 1

Comparison of energy storage performance of the representative films

Materials	W_{rec}（J/cm^3）	η（%）	E_b（kV/cm）	Thermal stability range (℃)	Ref.
NBTM/STM	68.9	54.4	4300	20-200	This work
SBLTM	47.7	66.5	3307	30-110	[1]
$(Sr_{0.85}Bi_{0.1})Ti_{0.99}Mn_{0.01}O_3$	24.4	64.7	1982	30-110	[2]
$(Sr_{0.925}Bi_{0.05})Ti_{0.99}Mn_{0.01}O_3$	23.6	67.5	2281	-	[2]
BFMO-SBT	61	75	3000	-50-200	[3]
NKBT-BST	54.8	76.4	3846	20-200	[4]
BMT/NBT	53.9	74.3	4105	15-115	[5]
BMT-STO	109.7	80.6	3393	25-200	[6]

References

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